

## TSM4414

## 30V N-Channel MOSFET



SOP-8

#### Pin Definition:

- 1. Source
- 2. Source
- 3. Source
- 4. Gate
- 5, 6, 7, 8. Drain

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
30	26 @ V <sub>GS</sub> = 10V	8.5	
	40 @ V <sub>GS</sub> = 4.5V	5	

#### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

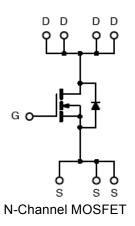
#### **Application**

- High-Side DC/DC Conversion
- Notebook
- Sever

#### **Ordering Information**

Part No.	Package	Packing
TSM4414CS RL	SOP-8	2.5Kpcs / 13" Reel

#### **Block Diagram**



**Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current		I <sub>D</sub>	8.5	Α	
Pulsed Drain Current		I <sub>DM</sub>	40	Α	
Continuous Source Current (Diode Condu	uction) <sup>a,b</sup>	Is	1.0	Α	
Maying an Dayyar Discipation	Ta = 25°C	P <sub>D</sub>	3.0	W	
Maximum Power Dissipation	Ta = 75°C		2.1		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ <sub>JF</sub>	32	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	50	°C/W

#### Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \le 10$  sec.



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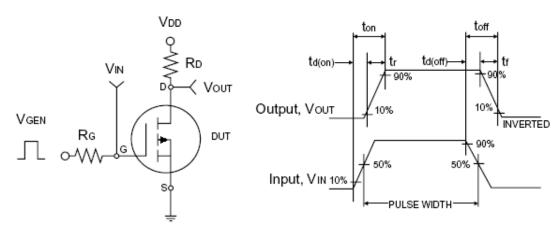


**Electrical Specifications** (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.4	3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>	-		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	μA
On-State Drain Current <sup>a</sup>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> = 10V	I <sub>D(ON)</sub>	30			Α
Drain-Source On-State Resistance	to Resistance <sup>a</sup> $V_{GS} = 10V$ , $I_D = 8.5A$	20	26			
Dialii-Source Oii-State Resistance	$V_{GS} = 4.5V, I_D = 5A$	$R_{DS(ON)}$	1	30	40	mΩ
Forward Transconductance <sup>a</sup>	$V_{DS} = 5V, I_{D} = 5A$	g <sub>fs</sub>	-	20		S
Diode Forward Voltage	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	$V_{SD}$	1	0.76	1.0	V
Dynamic <sup>b</sup>						
Total Gate Charge	\/ - 15\/   - 0.5A	$Q_g$		13		
Gate-Source Charge	$V_{DS} = V_{GS}, I_D = 250\mu A$ $V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{DS} = 24V, V_{GS} = 0V$ $V_{DS} \ge 5V, V_{GS} = 10V$ $V_{GS} = 10V, I_D = 8.5A$ $V_{GS} = 4.5V, I_D = 5A$ $V_{DS} = 5V, I_D = 5A$	$Q_gs$		4.2		nC
Gate-Drain Charge	V <sub>GS</sub> - 10V	$Q_{gd}$		3.1		
Input Capacitance	\/ - 45\/ \/ - 0\/	C <sub>iss</sub>	-	610		
Output Capacitance	, 66 ,	C <sub>oss</sub>	I	100		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	$C_{rss}$	I	77		
Switching <sup>c</sup>						
Turn-On Delay Time	V = 15V D = 15O	$t_{d(on)}$		9.1		
Turn-On Rise Time	$I_D = 1A, V_{GEN} = 10V,$	t <sub>r</sub>	1	16.5		nS
Turn-Off Delay Time		$t_{d(off)}$	1	23		113
Turn-Off Fall Time	116 012	t <sub>f</sub>		3.5		

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

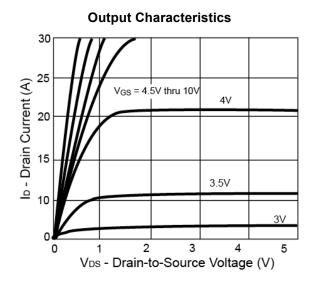




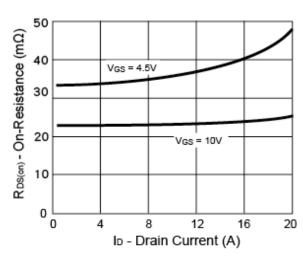
## 30V N-Channel MOSFET



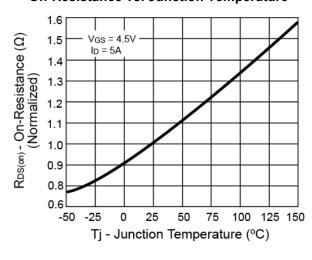
#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



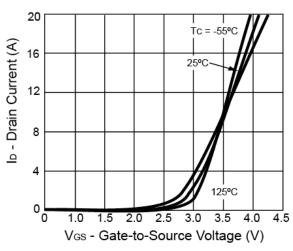
#### **On-Resistance vs. Drain Current**



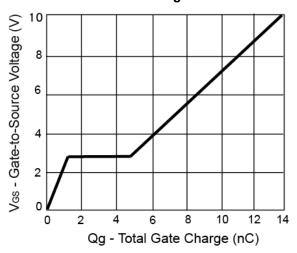
#### On-Resistance vs. Junction Temperature



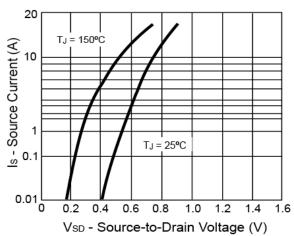
#### **Transfer Characteristics**



#### **Gate Charge**



#### Source-Drain Diode Forward Voltage







100

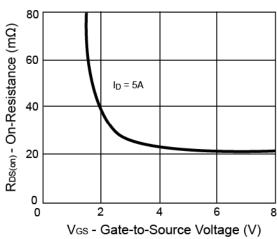
125 150





#### **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage



# 0.2 0.1 Source on the second of the second

25

50

Tj - Junction Temperature (°C)

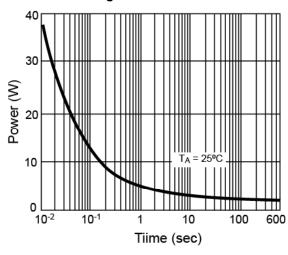
75

-0.4

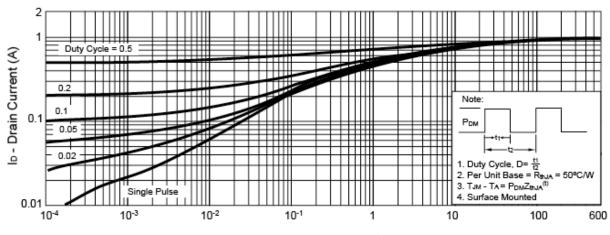
-50 -25

**Threshold Voltage** 

#### **Single Pulse Power**



#### Normalized Thermal Transient Impedance, Junction-to-Ambient



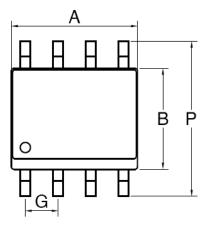
Square Wave Pulse Duration (sec)

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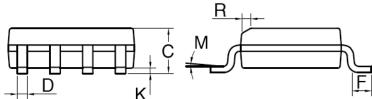
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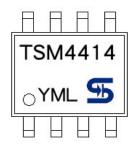
## **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05	0.05BSC	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



## **Marking Diagram**



Y = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

5/6

L = Lot Code

Version: B07



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